

# 74AUP2G17

Low-power dual Schmitt trigger

Rev. 02 — 10 January 2008

Product data sheet

## 1. General description

The 74AUP2G17 is a high-performance, low-power, low-voltage, Si-gate CMOS device, superior to most advanced CMOS compatible TTL families.

This device ensures a very low static and dynamic power consumption across the entire  $V_{CC}$  range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

The 74AUP2G17 provides two Schmitt trigger buffers. It is capable of transforming slowly changing input signals into sharply defined, jitter-free output signals.

The inputs switch at different points for positive and negative-going signals. The difference between the positive voltage  $V_{T+}$  and the negative voltage  $V_{T-}$  is defined as the input hysteresis voltage  $V_H$ .

## 2. Features

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
  - ◆ JESD8-12 (0.8 V to 1.3 V)
  - ◆ JESD8-11 (0.9 V to 1.65 V)
  - ◆ JESD8-7 (1.2 V to 1.95 V)
  - ◆ JESD8-5 (1.8 V to 2.7 V)
  - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
  - ◆ HBM JESD22-A114E Class 3A exceeds 5000 V
  - ◆ MM JESD22-A115-A exceeds 200 V
  - ◆ CDM JESD22-C101-C exceeds 1000 V
- Low static power consumption;  $I_{CC} = 0.9 \mu\text{A}$  (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of  $V_{CC}$
- $I_{OFF}$  circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from  $-40 \text{ }^\circ\text{C}$  to  $+85 \text{ }^\circ\text{C}$  and  $-40 \text{ }^\circ\text{C}$  to  $+125 \text{ }^\circ\text{C}$

### 3. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74AUP2G17GW	-40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363
74AUP2G17GM	-40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm	SOT886
74AUP2G17GF	-40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1 × 0.5 mm	SOT891

### 4. Marking

Table 2. Marking

Type number	Marking code
74AUP2G17GW	pV
74AUP2G17GM	pV
74AUP2G17GF	pV

### 5. Functional diagram

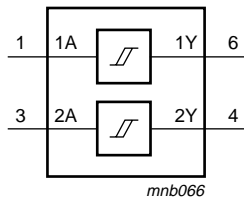


Fig 1. Logic symbol

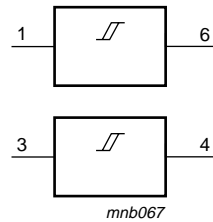


Fig 2. IEC logic symbol

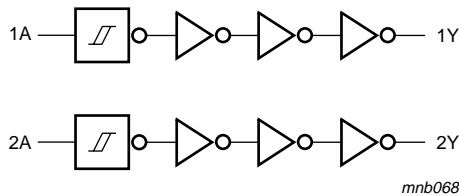
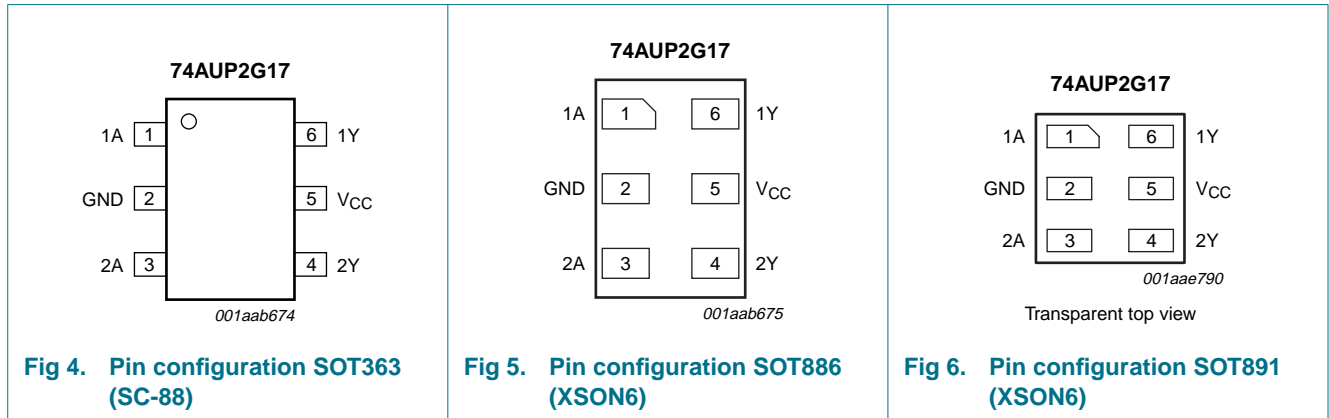


Fig 3. Logic diagram

## 6. Pinning information

### 6.1 Pinning



### 6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1A	1	data input
GND	2	ground (0 V)
2A	3	data input
2Y	4	data output
V <sub>CC</sub>	5	supply voltage
1Y	6	data output

## 7. Functional description

Table 4. Function table<sup>[1]</sup>

Input	Output
nA	nY
L	L
H	H

[1] H = HIGH voltage level;  
L = LOW voltage level.

## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+4.6	V
$I_{IK}$	input clamping current	$V_I < 0$ V	-	-50	mA
$V_I$	input voltage		[1] -0.5	+4.6	V
$I_{OK}$	output clamping current	$V_O > V_{CC}$ or $V_O < 0$ V	-	±50	mA
$V_O$	output voltage	Active mode and Power-down mode	[1] -0.5	+4.6	V
$I_O$	output current	$V_O = 0$ V to $V_{CC}$	-	±20	mA
$I_{CC}$	supply current		-	50	mA
$I_{GND}$	ground current		-	-50	mA
$T_{stg}$	storage temperature		-65	+150	°C
$P_{tot}$	total power dissipation	$T_{amb} = -40$ °C to +125 °C	[2] -	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SC-88 packages: above 87.5 °C the value of  $P_{tot}$  derates linearly with 4.0 mW/K.  
For XSON6 packages: above 45 °C the value of  $P_{tot}$  derates linearly with 2.4 mW/K.

## 9. Recommended operating conditions

**Table 6. Recommended operating conditions**

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		0.8	3.6	V
$V_I$	input voltage		0	3.6	V
$V_O$	output voltage	Active mode	0	$V_{CC}$	V
		Power-down mode; $V_{CC} = 0$ V	0	3.6	V
$T_{amb}$	ambient temperature		-40	+125	°C

## 10. Static characteristics

**Table 7. Static characteristics**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b><math>T_{amb} = 25</math> °C</b>						
$V_{OH}$	HIGH-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_O = -20$ µA; $V_{CC} = 0.8$ V to 3.6 V	$V_{CC} - 0.1$	-	-	V
		$I_O = -1.1$ mA; $V_{CC} = 1.1$ V	$0.75 \times V_{CC}$	-	-	V
		$I_O = -1.7$ mA; $V_{CC} = 1.4$ V	1.11	-	-	V
		$I_O = -1.9$ mA; $V_{CC} = 1.65$ V	1.32	-	-	V
		$I_O = -2.3$ mA; $V_{CC} = 2.3$ V	2.05	-	-	V
		$I_O = -3.1$ mA; $V_{CC} = 2.3$ V	1.9	-	-	V
		$I_O = -2.7$ mA; $V_{CC} = 3.0$ V	2.72	-	-	V
		$I_O = -4.0$ mA; $V_{CC} = 3.0$ V	2.6	-	-	V

**Table 7. Static characteristics ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 0.8 V to 3.6 V	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	0.3 × V <sub>CC</sub>	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.31	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.31	V
		I <sub>O</sub> = 2.3 mA; V <sub>CC</sub> = 2.3 V	-	-	0.31	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.44	V
		I <sub>O</sub> = 2.7 mA; V <sub>CC</sub> = 3.0 V	-	-	0.31	V
I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 3.0 V	-	-	0.44	V		
I <sub>I</sub>	input leakage current	V <sub>I</sub> = GND to 3.6 V; V <sub>CC</sub> = 0 V to 3.6 V	-	-	±0.1	μA
I <sub>OFF</sub>	power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V	-	-	±0.2	μA
ΔI <sub>OFF</sub>	additional power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V to 0.2 V	-	-	±0.2	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = GND or V <sub>CC</sub> ; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 0.8 V to 3.6 V	-	-	0.5	μA
ΔI <sub>CC</sub>	additional supply current	V <sub>I</sub> = V <sub>CC</sub> - 0.6 V; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 3.3 V	-	-	40	μA
C <sub>I</sub>	input capacitance	V <sub>I</sub> = GND or V <sub>CC</sub> ; V <sub>CC</sub> = 0 V to 3.6 V	-	1.1	-	pF
C <sub>O</sub>	output capacitance	V <sub>O</sub> = GND; V <sub>CC</sub> = 0 V	-	1.8	-	pF
<b>T<sub>amb</sub> = -40 °C to +85 °C</b>						
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 0.8 V to 3.6 V	V <sub>CC</sub> - 0.1	-	-	V
		I <sub>O</sub> = -1.1 mA; V <sub>CC</sub> = 1.1 V	0.7 × V <sub>CC</sub>	-	-	V
		I <sub>O</sub> = -1.7 mA; V <sub>CC</sub> = 1.4 V	1.03	-	-	V
		I <sub>O</sub> = -1.9 mA; V <sub>CC</sub> = 1.65 V	1.30	-	-	V
		I <sub>O</sub> = -2.3 mA; V <sub>CC</sub> = 2.3 V	1.97	-	-	V
		I <sub>O</sub> = -3.1 mA; V <sub>CC</sub> = 2.3 V	1.85	-	-	V
		I <sub>O</sub> = -2.7 mA; V <sub>CC</sub> = 3.0 V	2.67	-	-	V
I <sub>O</sub> = -4.0 mA; V <sub>CC</sub> = 3.0 V	2.55	-	-	V		
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 0.8 V to 3.6 V	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	0.3 × V <sub>CC</sub>	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.37	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.35	V
		I <sub>O</sub> = 2.3 mA; V <sub>CC</sub> = 2.3 V	-	-	0.33	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.45	V
		I <sub>O</sub> = 2.7 mA; V <sub>CC</sub> = 3.0 V	-	-	0.33	V
I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 3.0 V	-	-	0.45	V		
I <sub>I</sub>	input leakage current	V <sub>I</sub> = GND to 3.6 V; V <sub>CC</sub> = 0 V to 3.6 V	-	-	±0.5	μA
I <sub>OFF</sub>	power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V	-	-	±0.5	μA

**Table 7. Static characteristics ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$\Delta I_{OFF}$	additional power-off leakage current	$V_I$ or $V_O = 0\text{ V to }3.6\text{ V}$ ; $V_{CC} = 0\text{ V to }0.2\text{ V}$	-	-	$\pm 0.6$	$\mu\text{A}$
$I_{CC}$	supply current	$V_I = \text{GND or }V_{CC}$ ; $I_O = 0\text{ A}$ ; $V_{CC} = 0.8\text{ V to }3.6\text{ V}$	-	-	0.9	$\mu\text{A}$
$\Delta I_{CC}$	additional supply current	$V_I = V_{CC} - 0.6\text{ V}$ ; $I_O = 0\text{ A}$ ; $V_{CC} = 3.3\text{ V}$	-	-	50	$\mu\text{A}$
<b><math>T_{amb} = -40\text{ }^\circ\text{C to }+125\text{ }^\circ\text{C}</math></b>						
$V_{OH}$	HIGH-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_O = -20\text{ }\mu\text{A}$ ; $V_{CC} = 0.8\text{ V to }3.6\text{ V}$	$V_{CC} - 0.11$	-	-	V
		$I_O = -1.1\text{ mA}$ ; $V_{CC} = 1.1\text{ V}$	$0.6 \times V_{CC}$	-	-	V
		$I_O = -1.7\text{ mA}$ ; $V_{CC} = 1.4\text{ V}$	0.93	-	-	V
		$I_O = -1.9\text{ mA}$ ; $V_{CC} = 1.65\text{ V}$	1.17	-	-	V
		$I_O = -2.3\text{ mA}$ ; $V_{CC} = 2.3\text{ V}$	1.77	-	-	V
		$I_O = -3.1\text{ mA}$ ; $V_{CC} = 2.3\text{ V}$	1.67	-	-	V
		$I_O = -2.7\text{ mA}$ ; $V_{CC} = 3.0\text{ V}$	2.40	-	-	V
$V_{OL}$	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_O = 20\text{ }\mu\text{A}$ ; $V_{CC} = 0.8\text{ V to }3.6\text{ V}$	-	-	0.11	V
		$I_O = 1.1\text{ mA}$ ; $V_{CC} = 1.1\text{ V}$	-	-	$0.33 \times V_{CC}$	V
		$I_O = 1.7\text{ mA}$ ; $V_{CC} = 1.4\text{ V}$	-	-	0.41	V
		$I_O = 1.9\text{ mA}$ ; $V_{CC} = 1.65\text{ V}$	-	-	0.39	V
		$I_O = 2.3\text{ mA}$ ; $V_{CC} = 2.3\text{ V}$	-	-	0.36	V
		$I_O = 3.1\text{ mA}$ ; $V_{CC} = 2.3\text{ V}$	-	-	0.50	V
		$I_O = 2.7\text{ mA}$ ; $V_{CC} = 3.0\text{ V}$	-	-	0.36	V
$I_I$	input leakage current	$V_I = \text{GND to }3.6\text{ V}$ ; $V_{CC} = 0\text{ V to }3.6\text{ V}$	-	-	$\pm 0.75$	$\mu\text{A}$
		$V_I$ or $V_O = 0\text{ V to }3.6\text{ V}$ ; $V_{CC} = 0\text{ V}$	-	-	$\pm 0.75$	$\mu\text{A}$
$I_{OFF}$	power-off leakage current	$V_I$ or $V_O = 0\text{ V to }3.6\text{ V}$ ; $V_{CC} = 0\text{ V}$	-	-	$\pm 0.75$	$\mu\text{A}$
$\Delta I_{OFF}$	additional power-off leakage current	$V_I$ or $V_O = 0\text{ V to }3.6\text{ V}$ ; $V_{CC} = 0\text{ V to }0.2\text{ V}$	-	-	$\pm 0.75$	$\mu\text{A}$
$I_{CC}$	supply current	$V_I = \text{GND or }V_{CC}$ ; $I_O = 0\text{ A}$ ; $V_{CC} = 0.8\text{ V to }3.6\text{ V}$	-	-	1.4	$\mu\text{A}$
$\Delta I_{CC}$	additional supply current	$V_I = V_{CC} - 0.6\text{ V}$ ; $I_O = 0\text{ A}$ ; $V_{CC} = 3.3\text{ V}$	-	-	75	$\mu\text{A}$

## 11. Dynamic characteristics

**Table 8. Dynamic characteristics**

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 8](#)

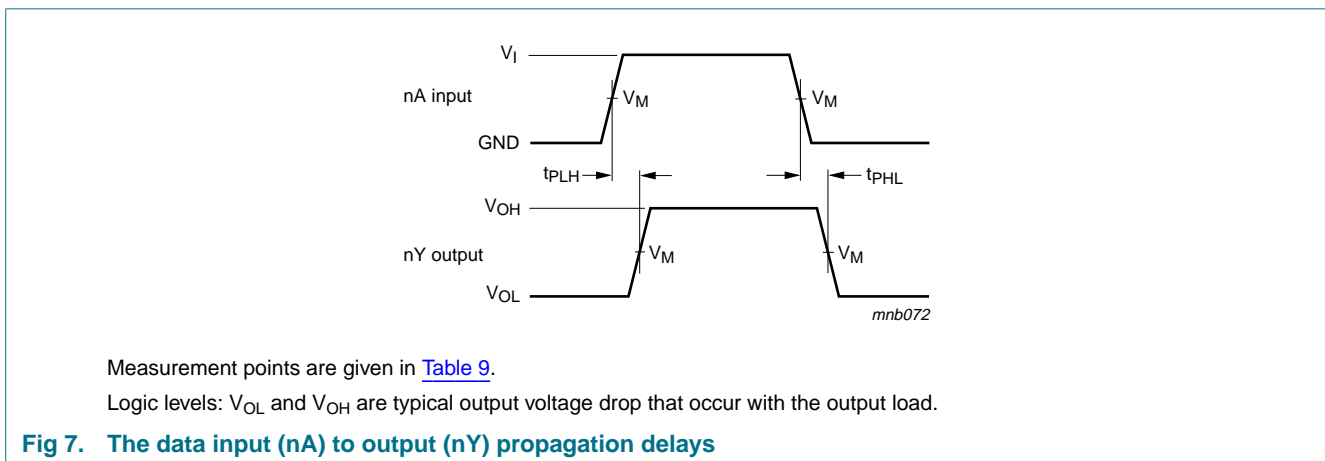
Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max (85 °C)	Max (125 °C)	
<b>C<sub>L</sub> = 5 pF</b>									
t <sub>pd</sub>	propagation delay	nA to nY; see <a href="#">Figure 7</a> <sup>[2]</sup>							
		V <sub>CC</sub> = 0.8 V	-	19.0	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	2.6	5.7	10.6	2.5	10.9	11.1	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	2.4	4.2	6.5	2.3	7.1	7.4	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	2.0	3.6	5.5	1.9	6.1	6.3	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.9	3.0	4.2	1.8	4.6	4.8	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	1.8	2.7	3.6	1.5	3.8	4.0	ns
<b>C<sub>L</sub> = 10 pF</b>									
t <sub>pd</sub>	propagation delay	nA to nY; see <a href="#">Figure 7</a> <sup>[2]</sup>							
		V <sub>CC</sub> = 0.8 V	-	22.5	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	2.9	6.6	12.4	2.7	12.9	13.0	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	2.6	4.8	7.8	2.4	8.3	8.7	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	2.5	4.2	6.3	2.4	6.8	7.1	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	2.3	3.5	4.8	2.1	5.3	5.6	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.1	3.3	4.4	2.0	4.6	4.8	ns
<b>C<sub>L</sub> = 15 pF</b>									
t <sub>pd</sub>	propagation delay	nA to nY; see <a href="#">Figure 7</a> <sup>[2]</sup>							
		V <sub>CC</sub> = 0.8 V	-	26.0	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	3.2	7.4	14.1	3.1	14.7	14.9	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	3.1	5.4	8.7	2.8	9.5	9.9	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	2.7	4.7	7.1	2.7	7.8	8.2	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	2.6	4.0	5.6	2.5	6.0	6.3	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.5	3.7	4.9	2.2	5.2	5.5	ns
<b>C<sub>L</sub> = 30 pF</b>									
t <sub>pd</sub>	propagation delay	nA to nY; see <a href="#">Figure 7</a> <sup>[2]</sup>							
		V <sub>CC</sub> = 0.8 V	-	36.3	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	3.9	9.7	19.0	3.7	19.8	20.1	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	3.5	7.0	11.2	3.6	12.4	13.0	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	3.5	6.0	9.2	3.4	10.1	10.7	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	3.4	5.1	7.0	3.2	7.5	7.9	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	3.3	4.8	6.2	3.1	7.1	7.5	ns

**Table 8. Dynamic characteristics ...continued**  
 Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 8](#)

Symbol	Parameter	Conditions	25 °C			−40 °C to +125 °C			Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max (85 °C)	Max (125 °C)	
<b>C<sub>L</sub> = 5 pF, 10 pF, 15 pF and 30 pF</b>									
C <sub>PD</sub>	power dissipation capacitance	f <sub>i</sub> = 1 MHz; V <sub>I</sub> = GND to V <sub>CC</sub> <sup>[3]</sup>							
		V <sub>CC</sub> = 0.8 V	-	2.9	-	-	-	-	pF
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	3.0	-	-	-	-	pF
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	3.2	-	-	-	-	pF
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	3.4	-	-	-	-	pF
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	4.0	-	-	-	-	pF
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	4.5	-	-	-	-	pF

- [1] All typical values are measured at nominal V<sub>CC</sub>.
- [2] t<sub>pd</sub> is the same as t<sub>PLH</sub> and t<sub>PHL</sub>.
- [3] C<sub>PD</sub> is used to determine the dynamic power dissipation (P<sub>D</sub> in μW).  
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$  where:  
 f<sub>i</sub> = input frequency in MHz;  
 f<sub>o</sub> = output frequency in MHz;  
 C<sub>L</sub> = output load capacitance in pF;  
 V<sub>CC</sub> = supply voltage in V;  
 N = number of inputs switching;  
 $\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of the outputs.

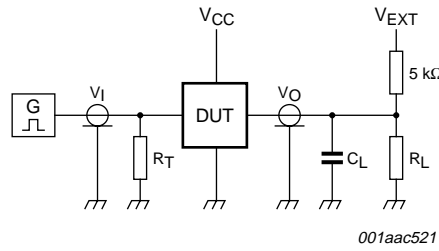
## 12. Waveforms



**Table 9. Measurement points**

Supply voltage	Output	Input		
V <sub>CC</sub>	V <sub>M</sub>	V <sub>M</sub>	V <sub>I</sub>	t <sub>r</sub> = t <sub>f</sub>
0.8 V to 3.6 V	0.5 × V <sub>CC</sub>	0.5 × V <sub>CC</sub>	V <sub>CC</sub>	≤ 3.0 ns





Test data is given in [Table 10](#).

Definitions for test circuit:

$R_L$  = Load resistance.

$C_L$  = Load capacitance including jig and probe capacitance.

$R_T$  = Termination resistance should be equal to the output impedance  $Z_o$  of the pulse generator.

$V_{EXT}$  = External voltage for measuring switching times.

**Fig 8. Load circuitry for switching times**

**Table 10. Test data**

Supply voltage	Load		$V_{EXT}$		
$V_{CC}$	$C_L$	$R_L$ [1]	$t_{PLH}$ , $t_{PHL}$	$t_{PZH}$ , $t_{PHZ}$	$t_{PZL}$ , $t_{PLZ}$
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times  $R_L = 5 \text{ k}\Omega$ , for measuring propagation delays, setup and hold times and pulse width  $R_L = 1 \text{ M}\Omega$ .

### 13. Transfer characteristics

**Table 11. Transfer characteristics**

Voltages are referenced to GND (ground = 0 V; for test circuit see [Figure 8](#)).

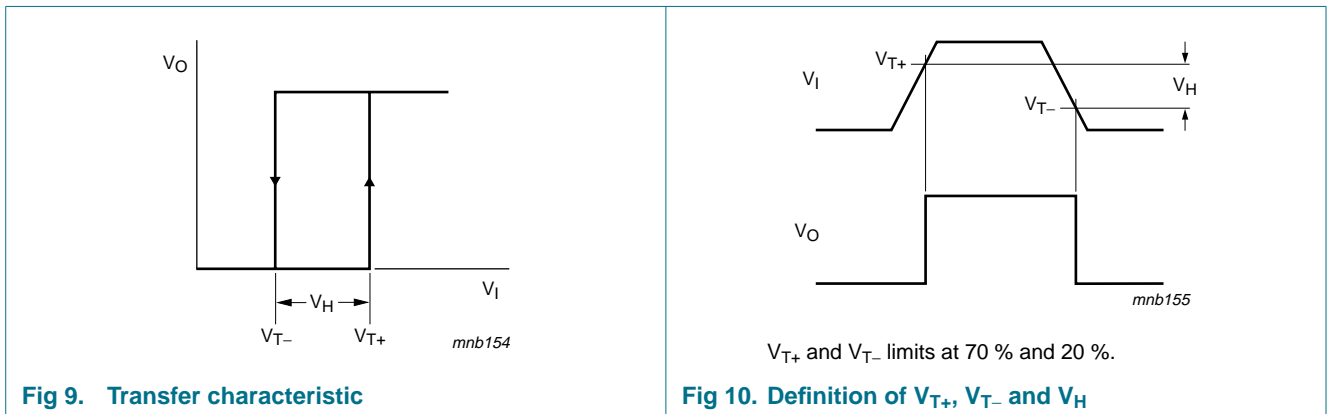
Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ	Max	Min	Max (85 °C)	Max (125 °C)	
$V_{T+}$	positive-going threshold voltage	see <a href="#">Figure 9</a> and <a href="#">Figure 10</a>							
		$V_{CC} = 0.8 \text{ V}$	0.30	-	0.60	0.30	0.60	0.62	V
		$V_{CC} = 1.1 \text{ V}$	0.53	-	0.90	0.53	0.90	0.92	V
		$V_{CC} = 1.4 \text{ V}$	0.74	-	1.11	0.74	1.11	1.13	V
		$V_{CC} = 1.65 \text{ V}$	0.91	-	1.29	0.91	1.29	1.31	V
		$V_{CC} = 2.3 \text{ V}$	1.37	-	1.77	1.37	1.77	1.80	V
$V_{T-}$	negative-going threshold voltage	see <a href="#">Figure 9</a> and <a href="#">Figure 10</a>							
		$V_{CC} = 0.8 \text{ V}$	0.10	-	0.60	0.10	0.60	0.60	V
		$V_{CC} = 1.1 \text{ V}$	0.26	-	0.65	0.26	0.65	0.65	V
		$V_{CC} = 1.4 \text{ V}$	0.39	-	0.75	0.39	0.75	0.75	V
		$V_{CC} = 1.65 \text{ V}$	0.47	-	0.84	0.47	0.84	0.84	V
		$V_{CC} = 2.3 \text{ V}$	0.69	-	1.04	0.69	1.04	1.04	V
	$V_{CC} = 3.0 \text{ V}$	0.88	-	1.24	0.88	1.24	1.24	V	

**Table 11. Transfer characteristics ...continued**

Voltages are referenced to GND (ground = 0 V; for test circuit see [Figure 8](#)).

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ	Max	Min	Max (85 °C)	Max (125 °C)	
$V_H$	hysteresis voltage ( $V_{T+} - V_{T-}$ ); see <a href="#">Figure 9</a> , <a href="#">Figure 10</a> , <a href="#">Figure 11</a> and <a href="#">Figure 12</a>	$V_{CC} = 0.8\text{ V}$	0.07	-	0.50	0.07	0.50	0.50	V
		$V_{CC} = 1.1\text{ V}$	0.08	-	0.46	0.08	0.46	0.46	V
		$V_{CC} = 1.4\text{ V}$	0.18	-	0.56	0.18	0.56	0.56	V
		$V_{CC} = 1.65\text{ V}$	0.27	-	0.66	0.27	0.66	0.66	V
		$V_{CC} = 2.3\text{ V}$	0.53	-	0.92	0.53	0.92	0.92	V
		$V_{CC} = 3.0\text{ V}$	0.79	-	1.31	0.79	1.31	1.31	V

### 14. Waveforms transfer characteristics



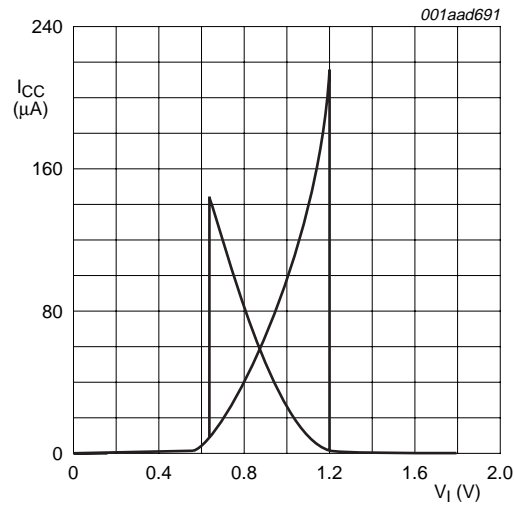


Fig 11. Typical transfer characteristics;  $V_{CC} = 1.8 V$

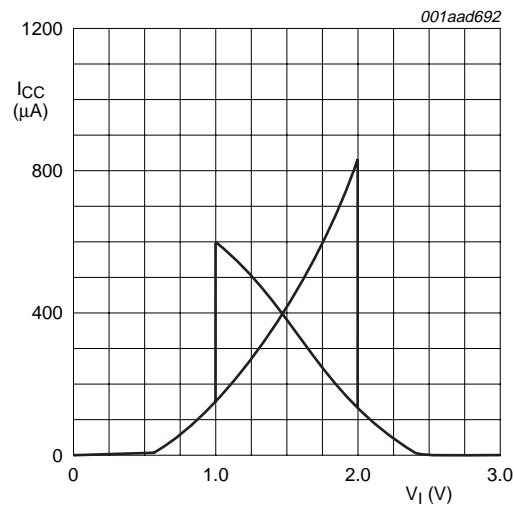


Fig 12. Typical transfer characteristics;  $V_{CC} = 3.0 V$

### 15. Application information

The slow input rise and fall times cause additional power dissipation, this can be calculated using the following formula:

$$P_{add} = f_i \times (t_r \times \Delta I_{CC(AV)} + t_f \times \Delta I_{CC(AV)}) \times V_{CC} \text{ where:}$$

$P_{add}$  = additional power dissipation ( $\mu W$ );

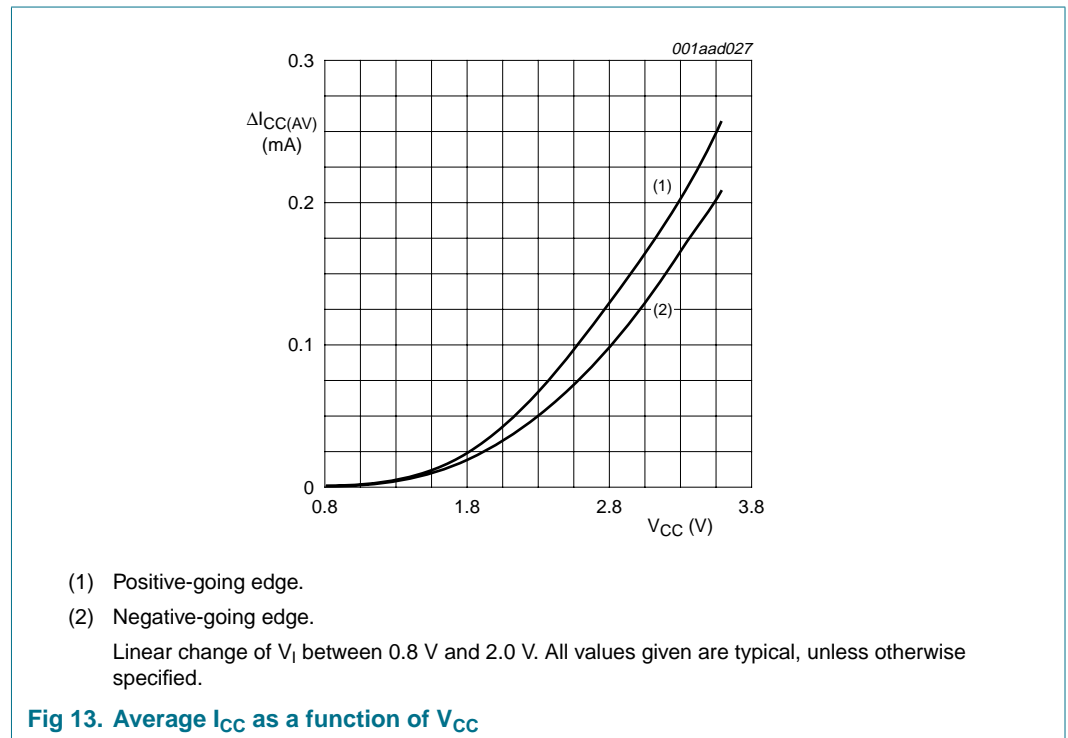
$f_i$  = input frequency (MHz);

$t_r$  = input rise time (ns); 10 % to 90 %;

$t_f$  = input fall time (ns); 90 % to 10 %;

$\Delta I_{CC(AV)}$  = average additional supply current ( $\mu A$ ).

Average  $\Delta I_{CC(AV)}$  differs with positive or negative input transitions, as shown in [Figure 13](#).



16. Package outline

Plastic surface-mounted package; 6 leads

SOT363

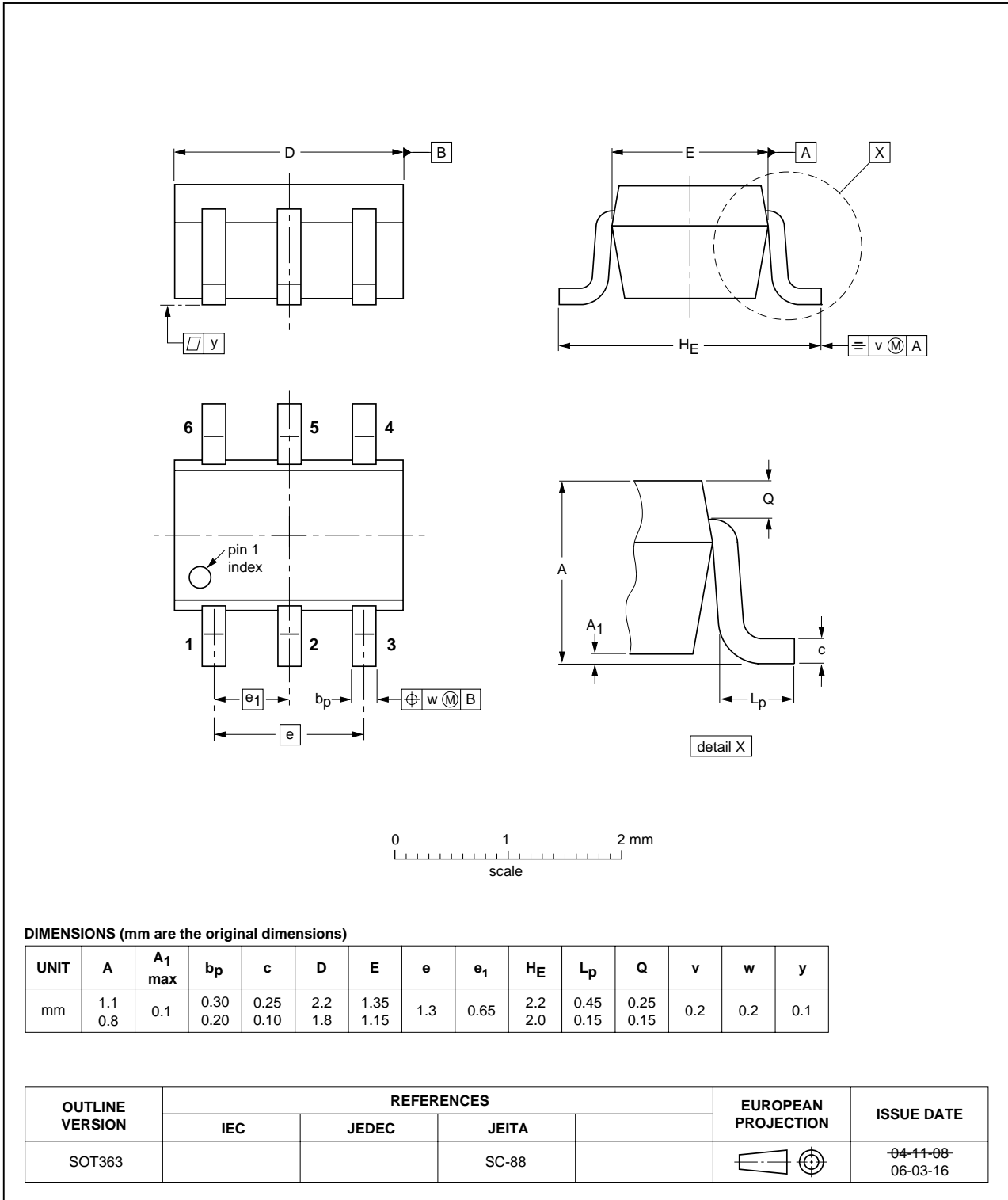


Fig 14. Package outline SOT363 (SC-88)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

SOT886

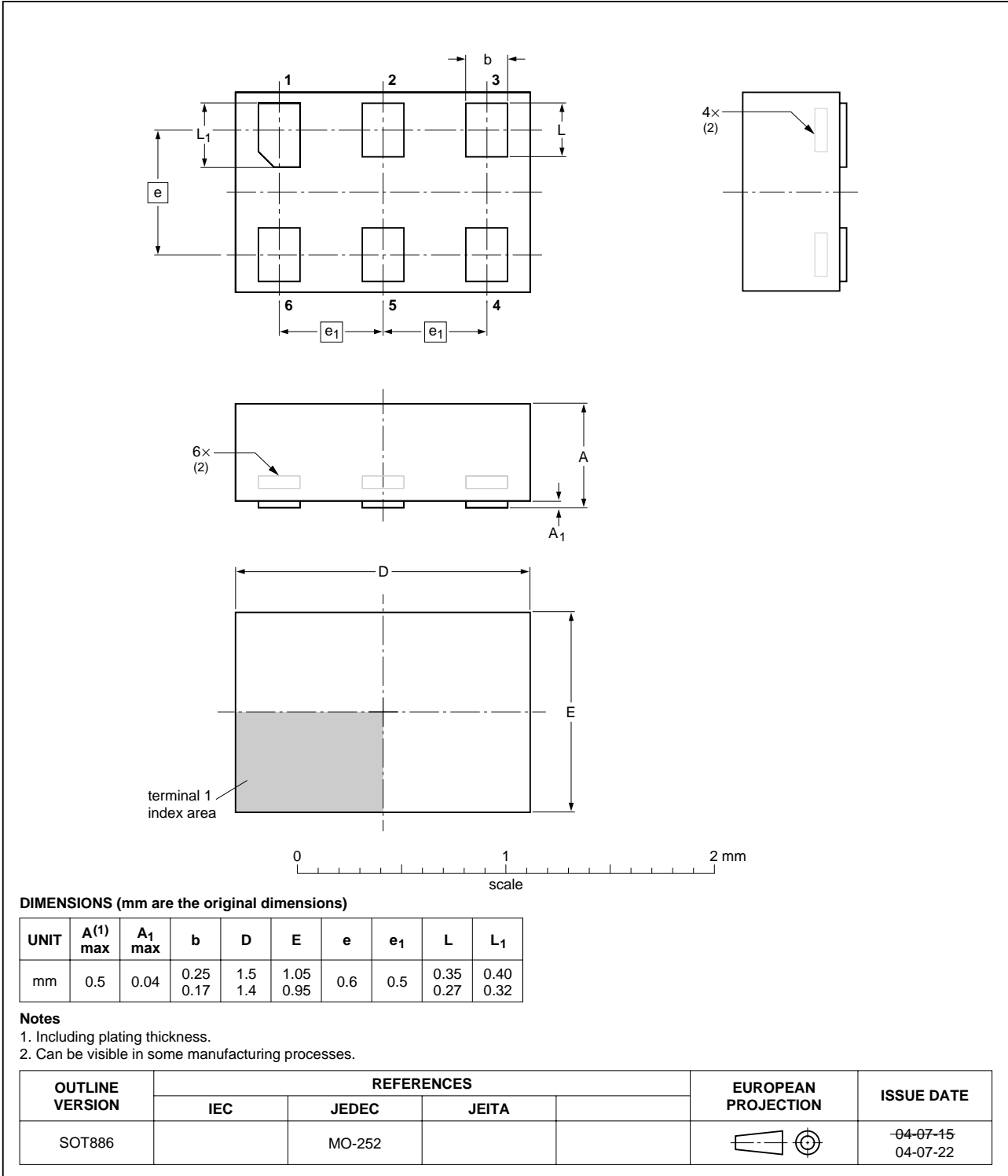


Fig 15. Package outline SOT886 (XSON6)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm

SOT891

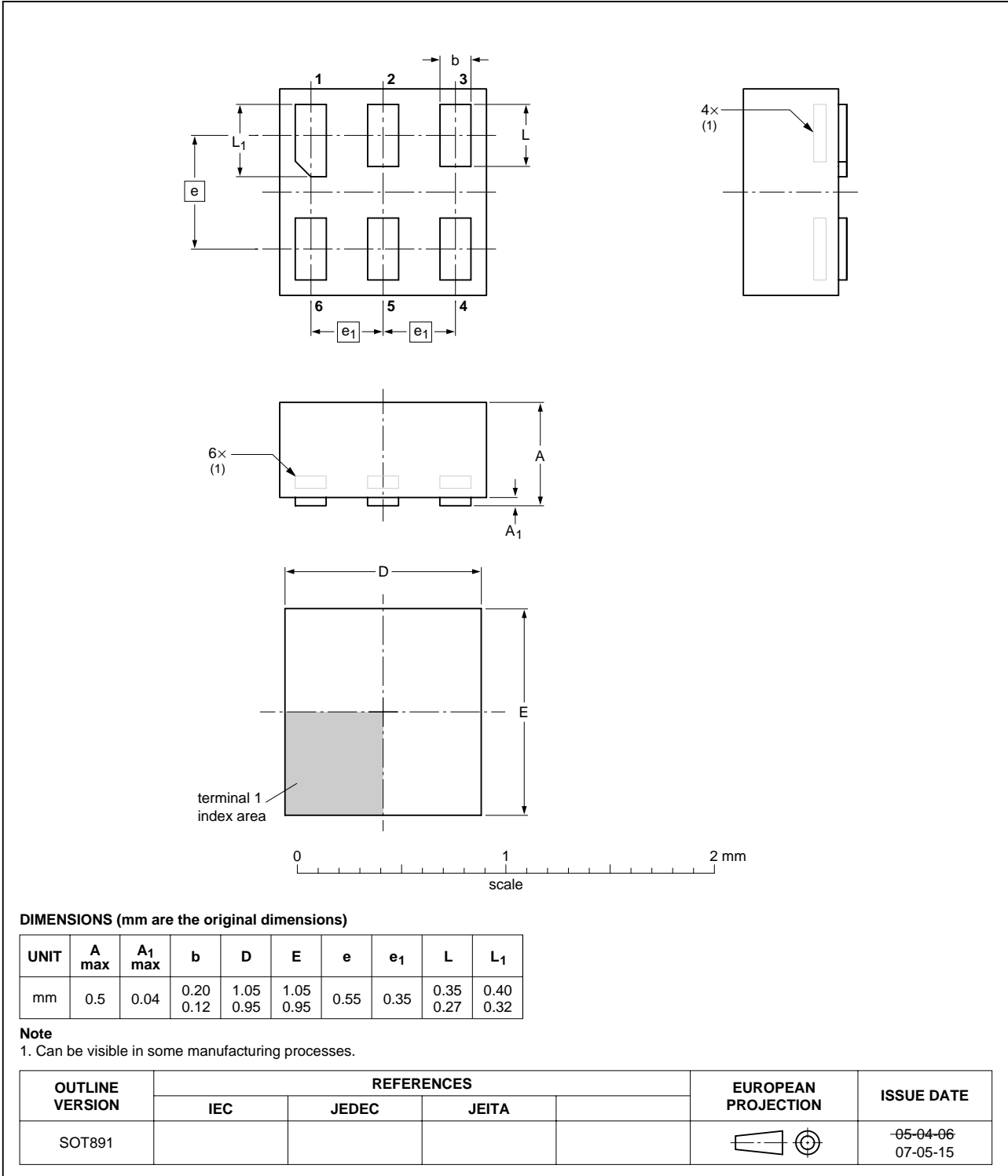


Fig 16. Package outline SOT891 (XSON6)

## 17. Abbreviations

Table 12. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

## 18. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP2G17_2	20080110	Product data sheet	-	74AUP2G17_1
Modifications:	<ul style="list-style-type: none"><li>• ESD HBM value modified in <a href="#">Section 2</a></li></ul>			
74AUP2G17_1	20061107	Product data sheet	-	-



## 19. Legal information

### 19.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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